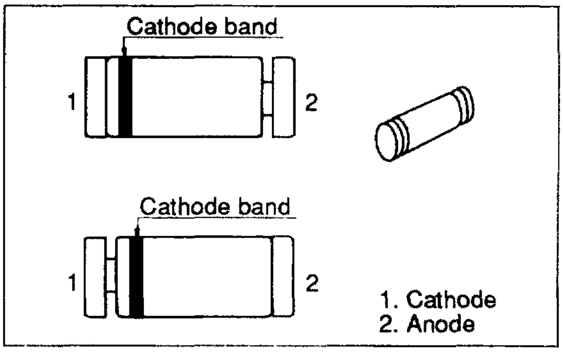
HSK120

Silicon Epitaxial Planar Diode for High Speed Switching

Features

- Low reverse recovery time. (t_{rr} =3.0ns max)
- LLD package is suitable for high density surface mounting and high speed assembly.

Outline



Ordering Information

Type No.	Cathode band	Package code
HSK120	White	LLD

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Value	Unit
Peak reverse voltage	V_{RM}	70	V
Reverse voltage	V_R	60	V
Peak forward current	I_{FM}	450	mA
Non-Repetitive peak forward surge current	I_{FSM} *	4	A
Average forward current	I_o	150	mA
Junction temperature	T_j	175	°C
Storage temperature	T_{stg}	-65 to +175	°C

* Within 1μs forward surge current.

Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Forward voltage	V_F	—	—	0.8	V	I_F = 10 mA
Reverse voltage	V_R	70	—	—	V	I_R = 5 μA
Reverse current	I_R	—	—	0.1	μA	V_R = 60 V
Capacitance	C	—	—	3.0	pF	V_R = 0 V, f = 1 MHz
Reverse recovery time	trr	—	—	3.0	ns	I_F = 10 mA, V_R = 6 V, R_L = 100 Ω, I_{rr} = 0.1 mA

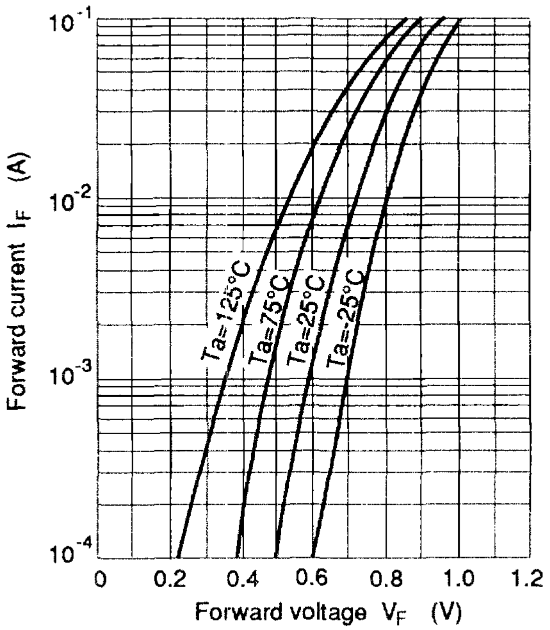


Fig.1 **Forward current Vs. Forward voltage**

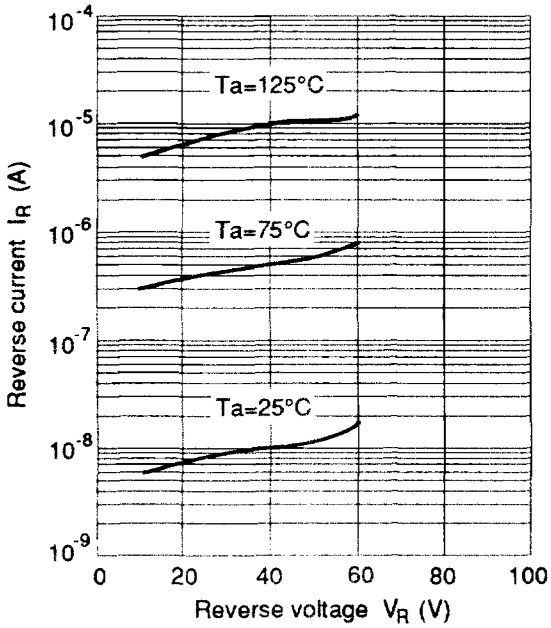


Fig.2 Reverse current Vs. Reverse voltage

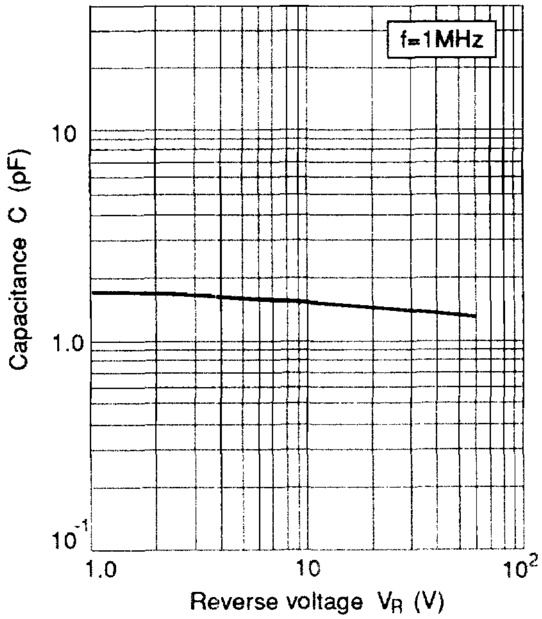


Fig.3 Capacitance Vs. Reverse voltage